

# NPN SILICON HIGH FREQUENCY TRANSISTOR

## DESCRIPTION

The **ASI BLX65S** is Designed for 12.5 V Class C Amplifier Applications in the 100 to 500 MHz Frequency Range.

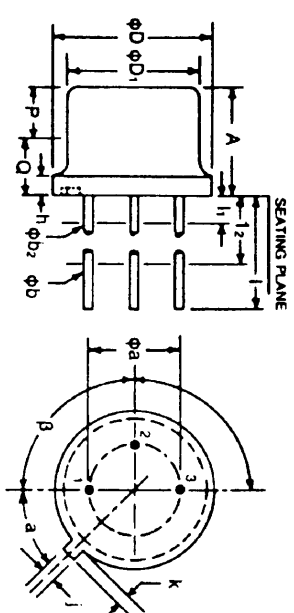
## FEATURES INCLUDE:

- Economical **TO-39** Package
- 8 dB Typical Gain
- Emitter Ballasting

## MAXIMUM RATINGS

$I_C$	750 mA
$V_{CBO}$	36 V
$P_{DISS}$	5.0 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+200^\circ C$
$\theta_{JC}$	$35^\circ C / W$

**PACKAGE STYLE TO-39**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
$\phi a$	0.190	0.210	4.83	5.33
A	0.240	0.260	6.10	6.60
$\phi b$	0.016	0.021	0.406	0.533
$\phi b_2$	0.016	0.019	0.406	0.483
$\phi D$	0.350	0.370	8.89	9.40
$\phi D_1$	0.315	0.335	8.00	8.51
h	0.009	0.125	0.229	3.18
i	0.028	0.034	0.711	0.864
k	0.029	0.040	0.737	1.02
l	0.500		12.70	
$l_1$		0.050		1.27
$l_2$	0.250		6.35	
P	0.100		2.54	
Q				
a	45° NOMINAL			
$\beta$	90° NOMINAL			

1 = EMITTER 2 = BASE  
3 = COLLECTOR (CASE)

## CHARACTERISTICS $T_A = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50 \text{ mA}$	16			V
$BV_{CES}$	$I_C = 50 \text{ mA}$	36			V
$BV_{EBO}$	$I_E = 1.0 \text{ mA}$	2.5			V
$I_{CBO}$	$V_{CB} = 15 \text{ V}$			1.0	mA
$h_{FE}$	$V_{CB} = 5.0 \text{ V}$ $I_C = 50 \text{ mA}$	20		200	---
$C_{OB}$	$V_{CB} = 12.5 \text{ V}$ $f = 1.0 \text{ MHz}$		15		pF
$G_{PE}$ $\eta_C$	$V_{CE} = 12.5 \text{ V}$ $P_{OUT} = 2.0 \text{ W}$ $f = 470 \text{ MHz}$	7.0	55		dB %